May 2008

# FAIRCHILD

SEMICONDUCTOR®

# FFPF08S60SN

## Features

- High Speed Switching,  $t_{rr} < 25$ ns @ I<sub>F</sub> = 8A
- High Reverse Voltage and High Reliability
- RoHS compliant

## Applications

- General Purpose
- Switching Mode Power Supply
- Boost Diode in continuous mode power factor corrections
- Power switching circuits





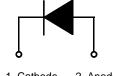
1. Cathode 2. Anode



characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as freewheeling of boost diode in

STEALTH<sup>™</sup> II Rectifier

switching power supplies and other power swithching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.



1. Cathode 2. Anode

### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

| Symbol                            | Parameter   | Ratings     | Units |  |
|-----------------------------------|---|-------------|-------|--|
| V <sub>RRM</sub>                  | Peak Repetitive Reverse Voltage                                 | 600         | V     |  |
| V <sub>RWM</sub>                  | Working Peak Reverse Voltage                                    | 600         | V     |  |
| V <sub>R</sub>                    | DC Blocking Voltage   | 600         | V     |  |
| I <sub>F(AV)</sub>                | Average Rectified Forward Current @ $T_{C} = 60^{\circ}C$       | 8           | А     |  |
| I <sub>FSM</sub>                  | Non-repetitive Peak Surge Current<br>60Hz Single Half-Sine Wave | 60          | А     |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                         | -65 to +150 | °C    |  |

## **Thermal Characteristics**

| Symbol              | Parameter                                    | Ratings | Units |
|---------------------|--|---------|-------|
| $R_{	ext{	heta}JC}$ | Maximum Thermal Resistance, Junction to Case | 6.8     | °C/W  |

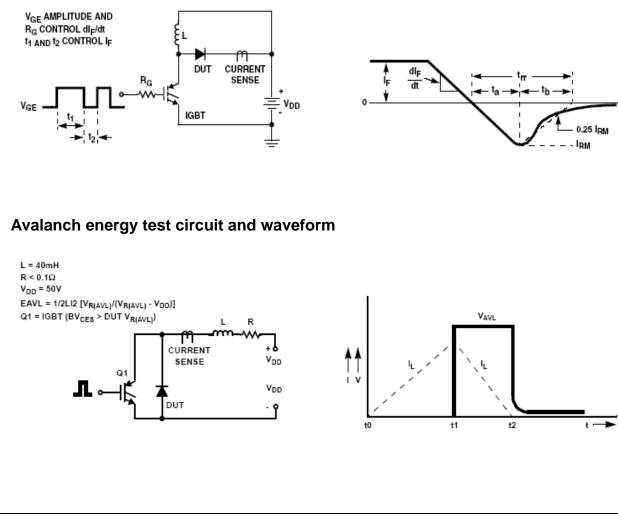
## Package Marking and Ordering Information

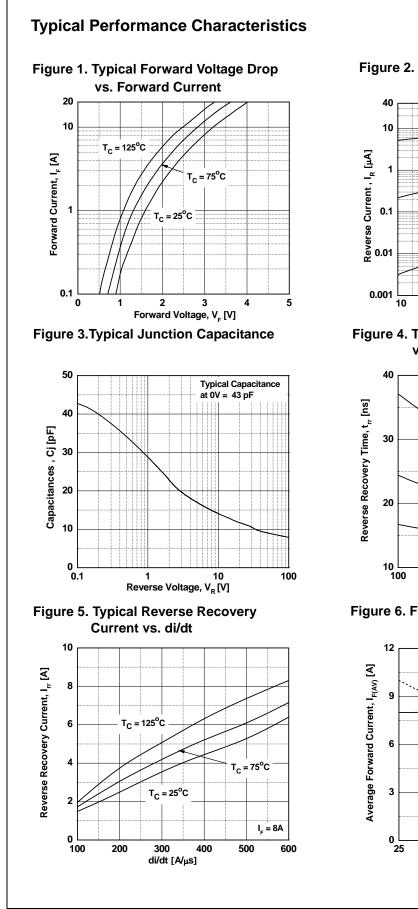
| Device Marking | Device        | Package   | Reel Size | Tape Width | Quantity |
|----------------|---------------|-----------|-----------|------------|----------|
| F08S60SN       | FFPF08S60SNTU | TO220F-2L | -         | -          | 50       |

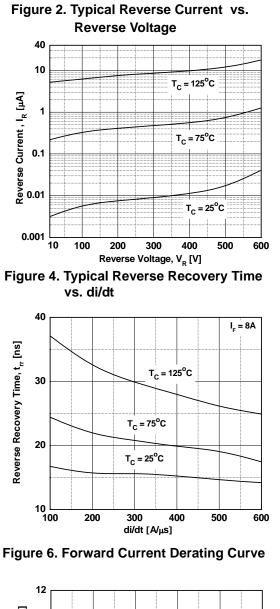
| Symbol  | Parameter   |   | Min. | Тур.                   | Max.              | Units         |
|---|---|---|------|------------------------|-------------------|---------------|
| V <sub>FM</sub> 1   | I <sub>F</sub> = 8A<br>I <sub>F</sub> = 8A                  | T <sub>C</sub> = 25°C<br>T <sub>C</sub> = 125°C |      | 2.7<br>2.1             | 3.4               | V             |
| I <sub>RM</sub> 1   | $V_{R} = 600V$ $V_{R} = 600V$                               | $T_{C} = 25^{\circ}C$<br>$T_{C} = 125^{\circ}C$ | -    | -                      | 100<br>500        | μA            |
| t <sub>rr</sub>   | I <sub>F</sub> = 1A, di/dt = 100A/µs, V <sub>R</sub> = 30V  | $T_C = 25^{\circ}C$                             | -    | 13                     | -                 | ns            |
| t <sub>rr</sub><br>I <sub>rr</sub><br>S factor<br>Q <sub>rr</sub> | I <sub>F</sub> = 8A, di/dt = 200A/µs, V <sub>R</sub> = 390V | T <sub>C</sub> = 25°C                           |      | 15<br>2.5<br>0.4<br>19 | 25<br>-<br>-<br>- | ns<br>A<br>nC |
| t <sub>rr</sub><br>I <sub>rr</sub><br>S factor<br>Q <sub>rr</sub> | I <sub>F</sub> = 8A, di/dt = 200A/µs, V <sub>R</sub> = 390V | T <sub>C</sub> = 125°C                          |      | 32<br>3.8<br>0.7<br>62 |                   | ns<br>A<br>nC |
| W <sub>AVL</sub>  | Avalanche Energy ( L = 40mH)                                |   | 10   | -                      | -                 | mJ            |

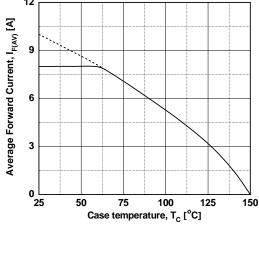
Notes: 1: Pulse: Test Pulse width = 300µs, Duty Cycle = 2%

# Trr test circuit and waveform



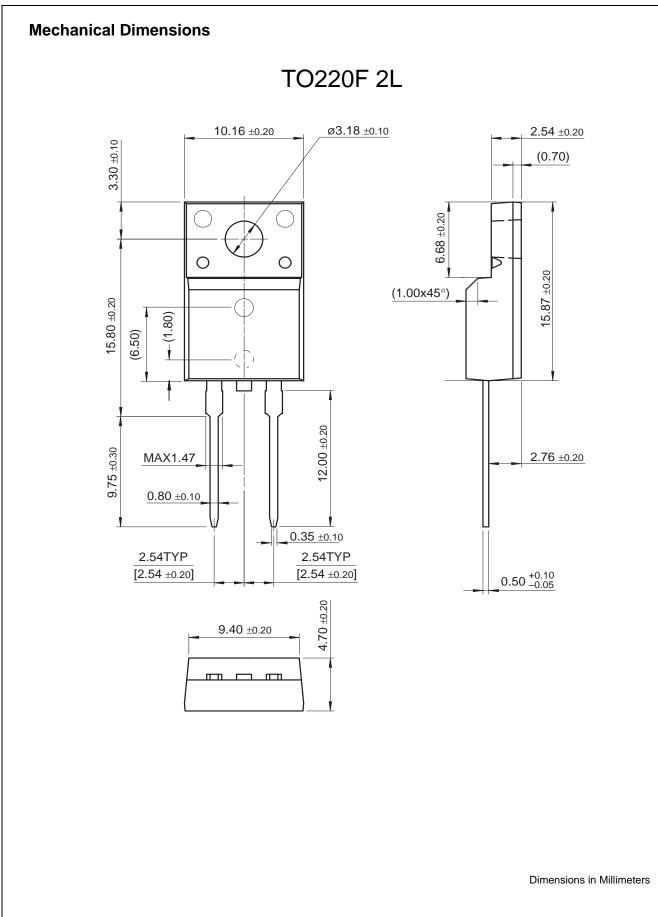






FFPF08S60SN Rev. A

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|--------------------------|------------------------|--|
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